

March 2011

FDS86140

N-Channel PowerTrench[®] MOSFET 100 V, 11.2 A, 9.8 m Ω

Features

- Max $r_{DS(on)} = 9.8 \text{ m}\Omega$ at $V_{GS} = 10 \text{ V}$, $I_D = 11.2 \text{ A}$
- Max $r_{DS(on)} = 16 \text{ m}\Omega$ at $V_{GS} = 6 \text{ V}$, $I_D = 9 \text{ A}$
- High performance trench technologh for extremely low r_{DS(on)}
- High power and current handing capability in a widely used surface mount package
- 100% UIL Tested
- RoHS Compliant

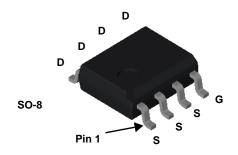


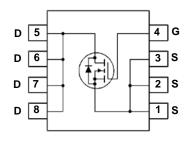
General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced Power Trench® process that has been optimized for $r_{DS(on)}$, switching performance and ruggedness.

Applications

- DC/DC Converters and Off-Line UPS
- Distributed Power Architectures and VRMs
- Primary Swith for 24 V and 48 V Systems
- High Voltage Synchronous Rectifier





MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted

Symbol	Parame		Ratings	Units	
V _{DS}	Drain to Source Voltage			100	V
V_{GS}	Gate to Source Voltage		±20	V	
	Drain Current -Continuous			11.2	A
'D	-Pulsed			50	
E _{AS}	Single Pulse Avalanche Energy		(Note 3)	264	mJ
В	Power Dissipation	T _C = 25 °C	(Note 1)	5.0	W
P_{D}	Power Dissipation	T _A = 25 °C	(Note 1a)	2.5	VV
T _J , T _{STG}	Operating and Storage Junction Temperature Range			-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	(Note 1)	25	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	50	C/VV

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDS86140	FDS86140	SO-8	13"	12 mm	2500 units

Electrical Characteristics $T_J = 25 \, ^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	100			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, referenced to 25 °C		70		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 80 V, V _{GS} = 0 V			1	μΑ
I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA

On Characteristics

V _{GS(th)}	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	2	2.7	4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I _D = 250 μA, referenced to 25 °C		-11		mV/°C
r _{DS(on)} Static		V _{GS} = 10 V, I _D = 11.2 A		8.1	9.8	
	Static Drain to Source On Resistance	$V_{GS} = 6 \text{ V}, I_{D} = 9 \text{ A}$		10.8	16	mΩ
	Static Drain to Source Off Nesistance	$V_{GS} = 10 \text{ V}, I_D = 11.2 \text{ A},$ $T_J = 125 ^{\circ}\text{C}$		13.1	17	11152
9 _{FS}	Forward Transconductance	V _{DS} = 10 V, I _D = 11.2 A		35		S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 50.V/V 0.V/	1940	2580	pF
C _{oss}	Output Capacitance	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1 \text{ MHz}$	440	585	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 1/1/12	20	30	pF
R _a	Gate Resistance		0.9		Ω

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		13.	7 25	ns
t _r	Rise Time	V _{DD} = 50 V, I _D = 11.2 A,	5.6	3 11	ns
t _{d(off)}	Turn-Off Delay Time	$V_{GS} = 10 \text{ V}, R_{GEN} = 6 \Omega$	23	38	ns
t _f	Fall Time		4.8	3 10	ns
Q_g	Total Gate Charge	V _{GS} = 0 V to 10 V	29	41	nC
Q_g	Total Gate Charge	$V_{GS} = 0 \text{ V to 5 V} V_{DD} = 50 \text{ V},$	16.	5 23	nC
Q _{gs}	Gate to Source Charge	I _D = 11.2 A	8.0)	nC
Q_{gd}	Gate to Drain "Miller" Charge		6.5	5	nC

Drain-Source Diode Characteristics

V _{SD} Source-Drain Diode Forward Voltage	Source Drain Diade Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = 11.2 \text{ A}$ (Note 2)	0.	8 1	.3	V
	$V_{GS} = 0 \text{ V, } I_{S} = 2 \text{ A}$ (Note 2)	0.	7 1	.2	۷	
t _{rr}	Reverse Recovery Time	I _E = 11.2 A, di/dt = 100 A/μs	5:	3 8	35 r	ns
Q _{rr}	Reverse Recovery Charge	- 1 _F = 11.2 A, α//αι = 100 A/μs		9 9	94 r	nC

^{1.} R_{0,1A} is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. R_{0,1C} is guaranteed by design while R_{0,CA} is determined by the user's board design.



a) 50 °C/W when mounted on a 1 in² pad of 2 oz copper.



b) 125 °C/W when mounted on a minimum pad.

^{2.} Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0%. 3. Starting T $_J$ = 25 °C, $\,$ L = 1 mH, I_{AS} = 23 A, V_{DD} = 90 V, V_{GS} = 10 V.

Typical Characteristics T_J = 25 °C unless otherwise noted

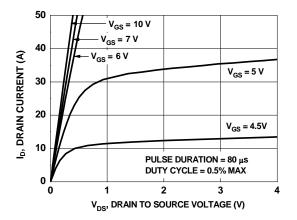


Figure 1. On Region Characteristics

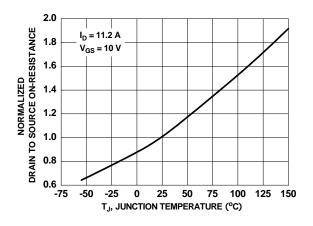


Figure 3. Normalized On Resistance vs Junction Temperature

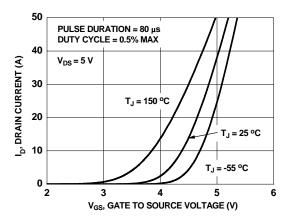


Figure 5. Transfer Characteristics

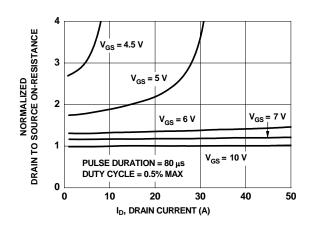


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

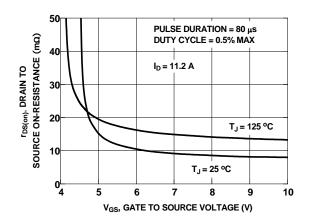


Figure 4. On-Resistance vs Gate to Source Voltage

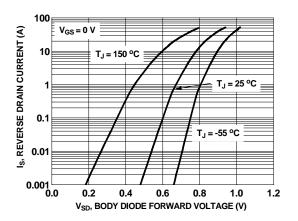


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25 °C unless otherwise noted

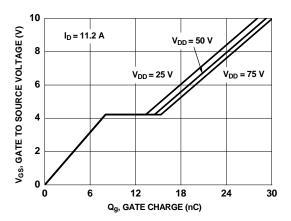


Figure 7. Gate Charge Characteristics

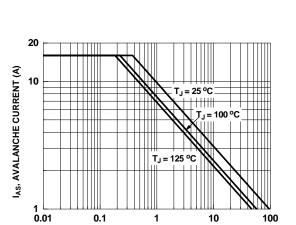


Figure 9. Unclamped Inductive Switching Capability

 \mathbf{t}_{AV} , TIME IN AVALANCHE (ms)

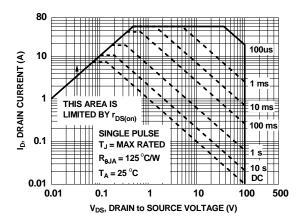


Figure 11. Forward Bias Safe Operating Area

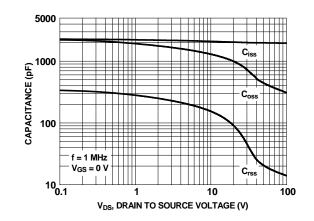


Figure 8. Capacitance vs Drain to Source Voltage

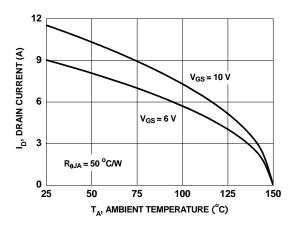


Figure 10. Maximum Continuous Drain Current vs Ambient Temperature

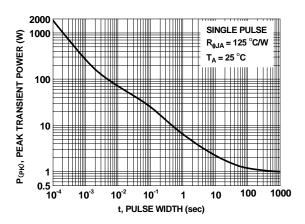


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25$ °C unless otherwise noted

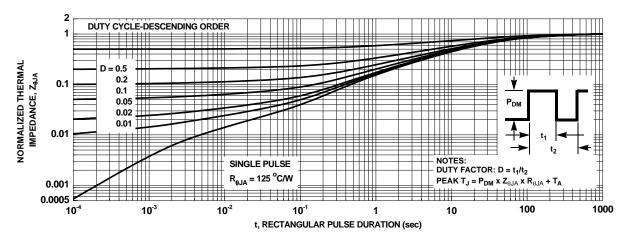
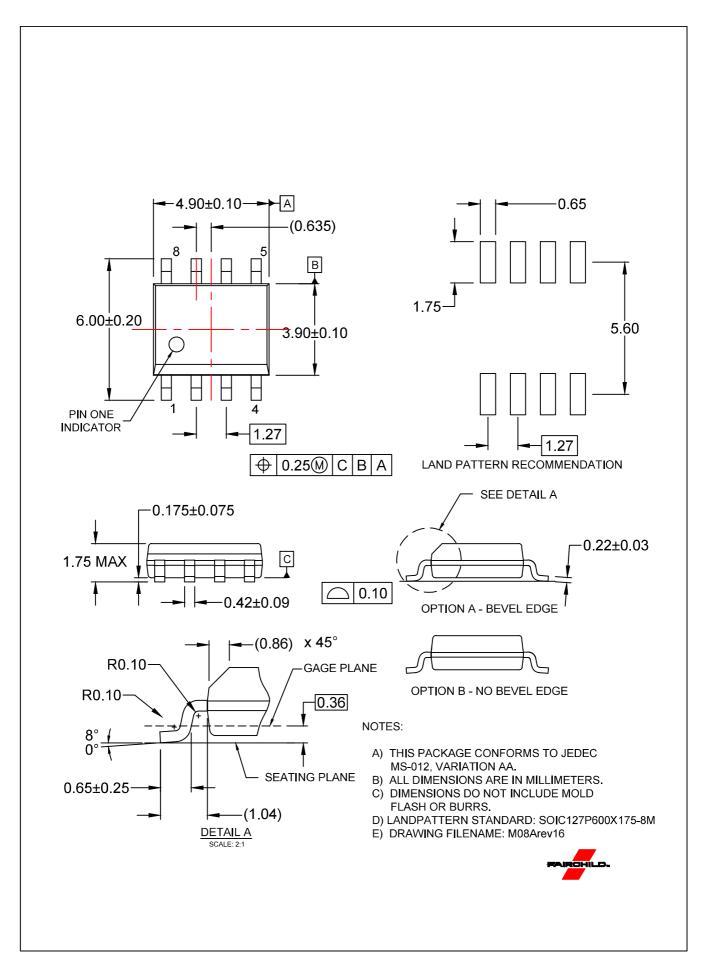


Figure 13. Junction-to-Ambient Transient Thermal Response Curve







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